

2/3

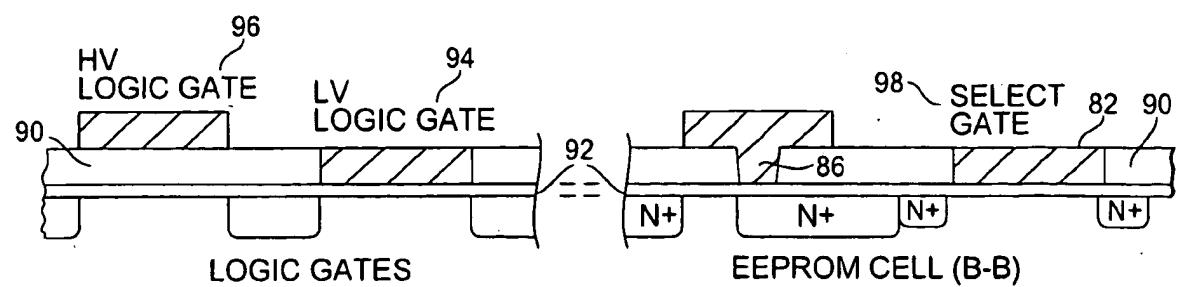
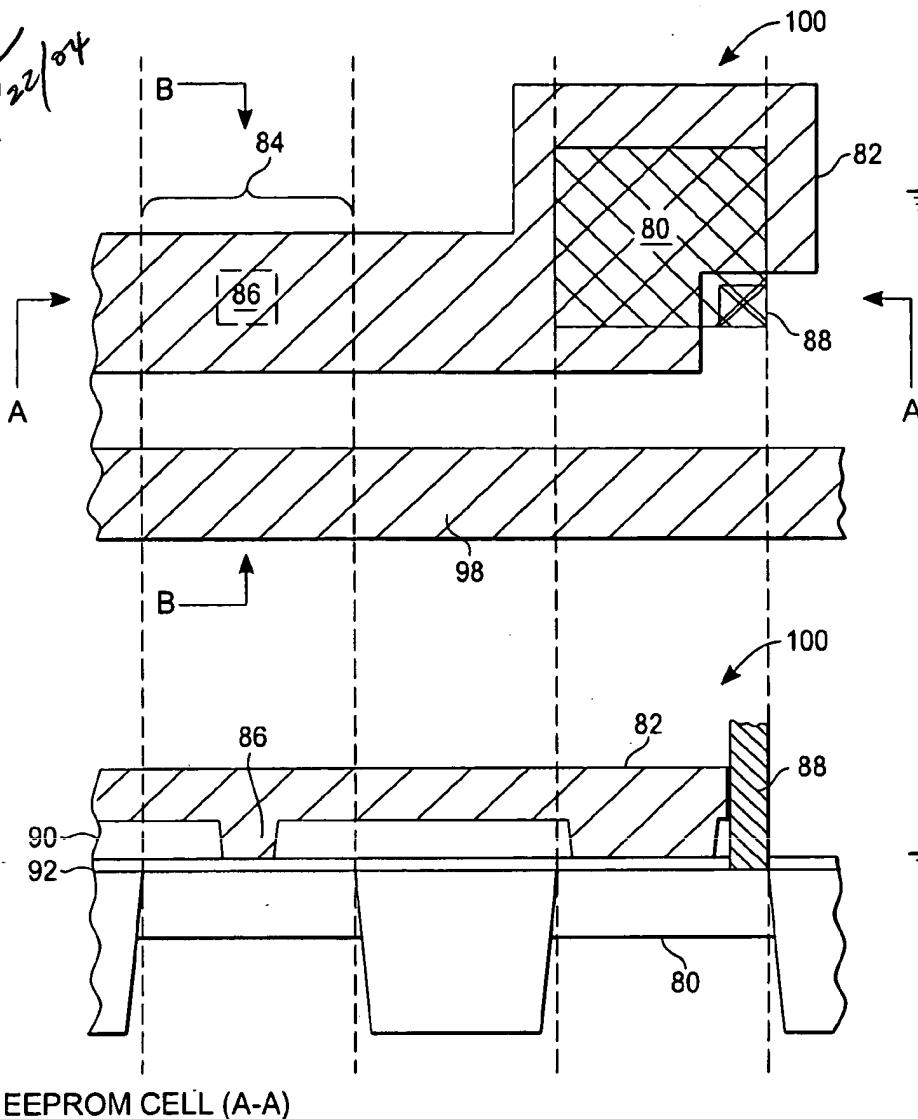
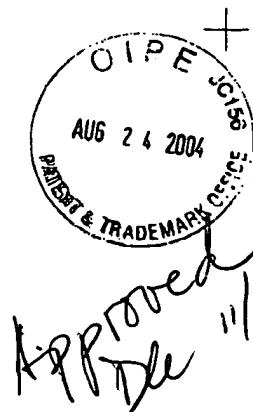


Fig. 2C

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Second
Area
ATM-262 Device

REPLACEMENT SHEET
Third
Area Device

First Area Device

3/3



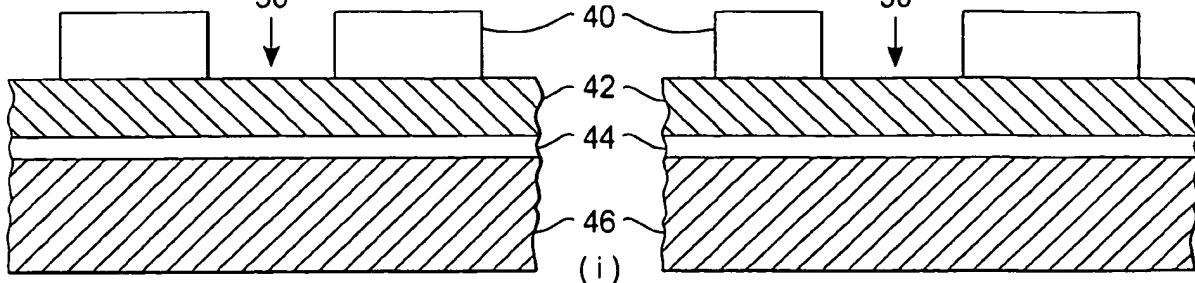
HIGH VOLTAGE MOS

50

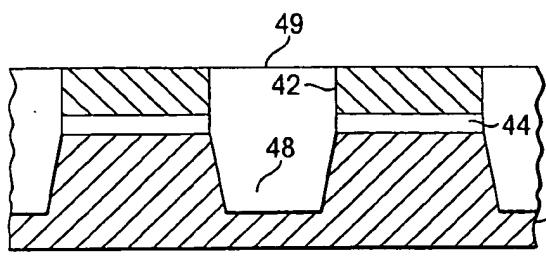
LOW VOLTAGE MOS

EEPROM CELL ALONG WORDLINE

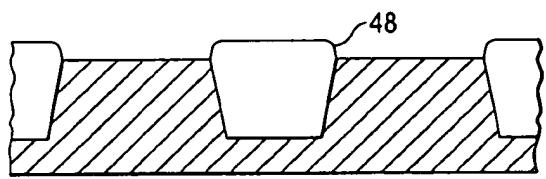
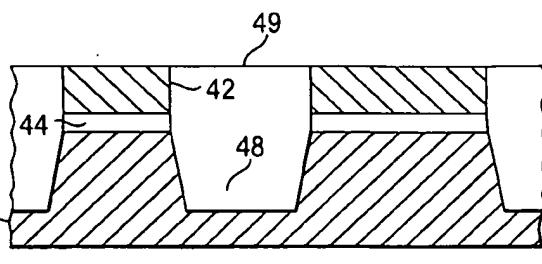
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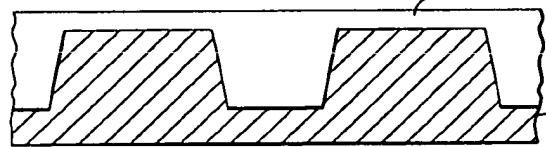
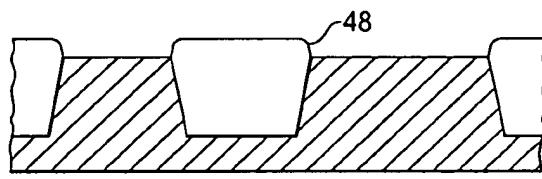
(i)



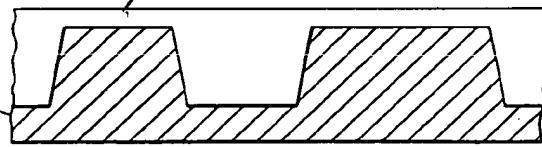
(ii)



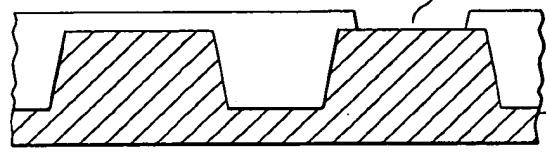
(iii)
68 HV gate oxide layer



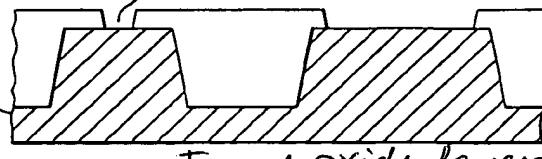
52 Exposed area



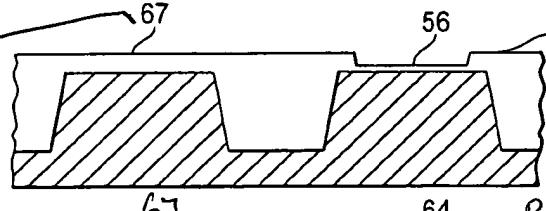
54 Exposed area.



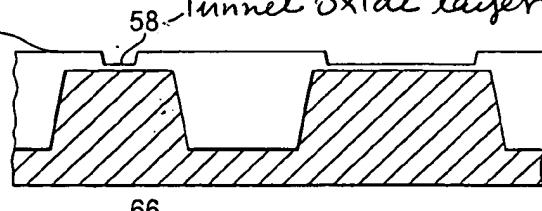
(v)



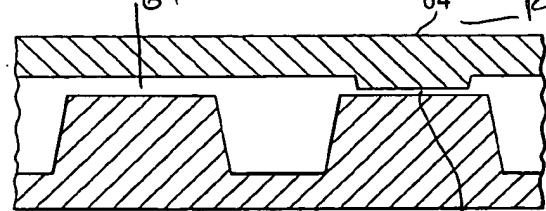
58 Tunnel oxide layer



(vi)



67 LV gate oxide layer



(vii)

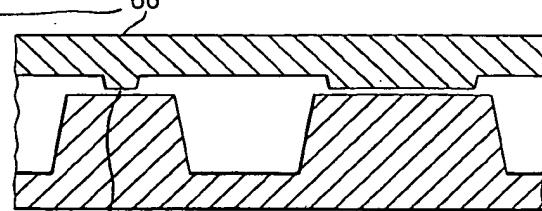


Fig. 3B

56

Fig. 3A

58

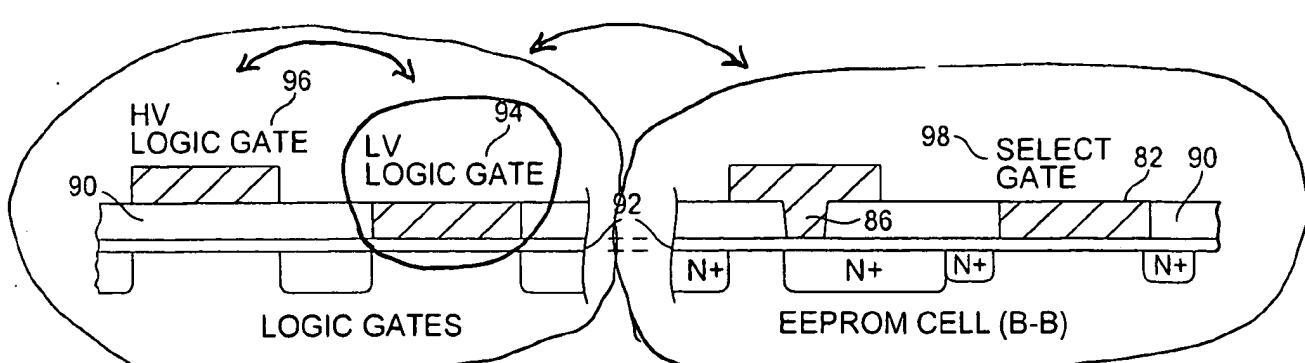
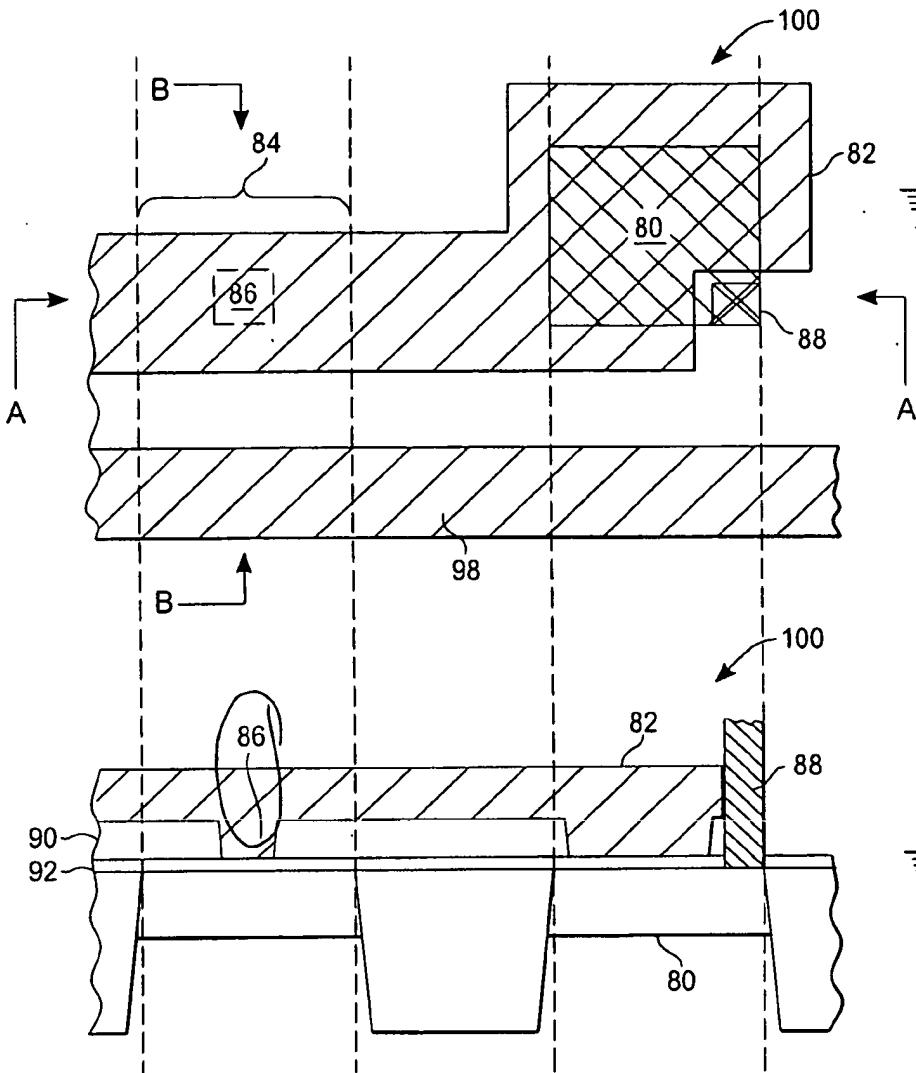
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ATM-262

ANNOTATED MARKED-UP DRAWINGS

2/3



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ANNOTATED MARKED-UP DRAWINGS

ATM-262



3/3

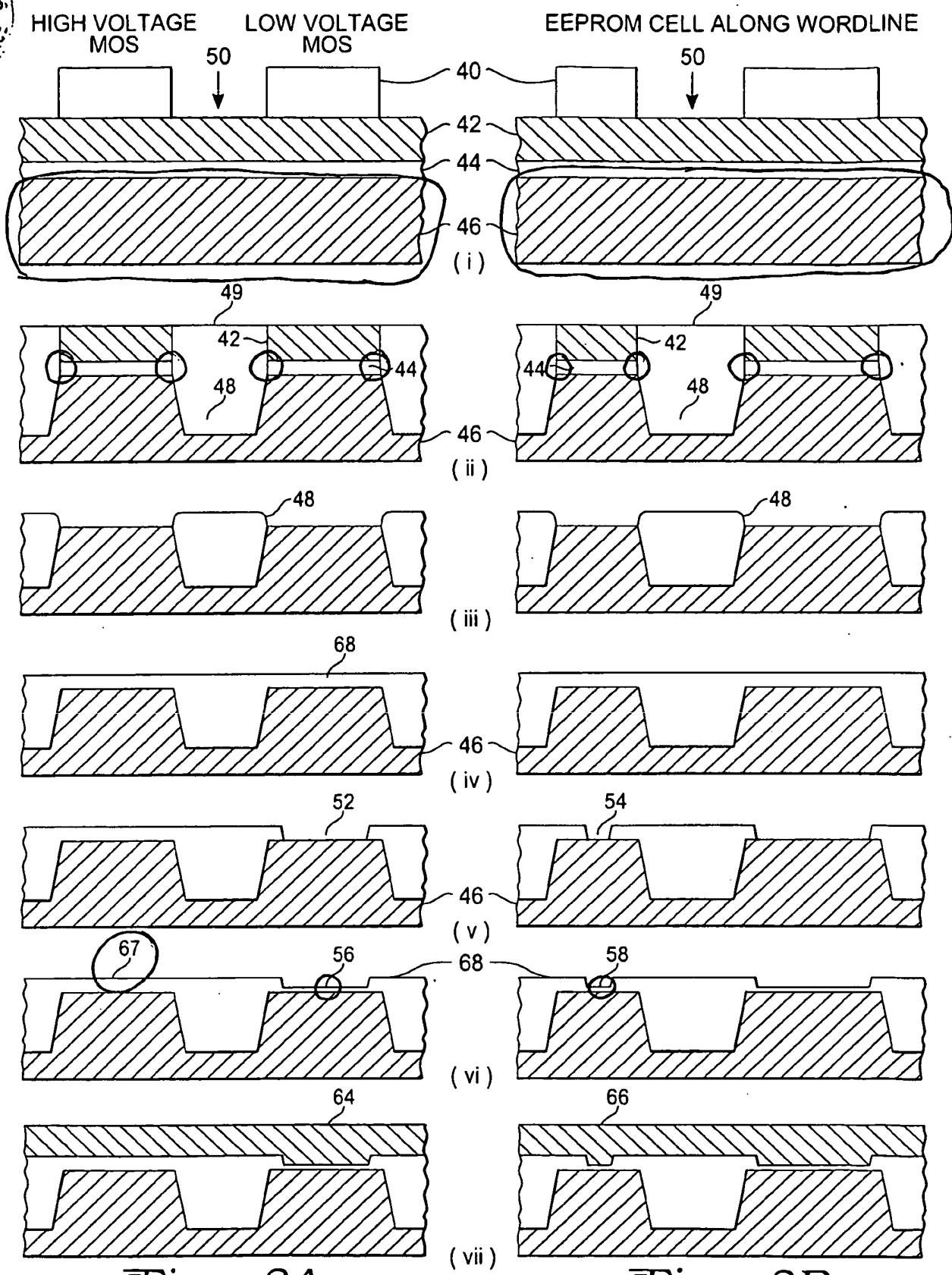


Fig._ 3A

Fig._ 3B